



# 2SA2040/2SC5707

## Bipolar Transistor (-50V, (-)8A, Low VCE(sat), (PNP)NPN Single TP/TP-FA

ON Semiconductor®

<http://onsemi.com>

### Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, flash

### Features

- Adoption of FBET and MBIT processes
- Large current capacitance
- Low collector-to-emitter saturation voltage
- High-speed switching
- High allowable power dissipation

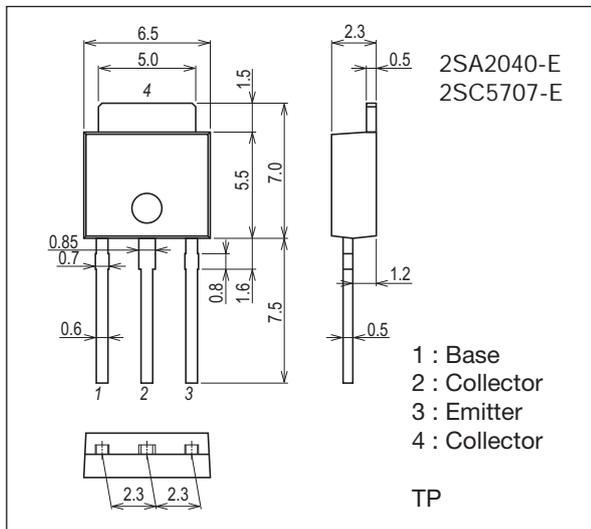
### Specifications ( ) : 2SA2040

#### Absolute Maximum Ratings at Ta=25°C

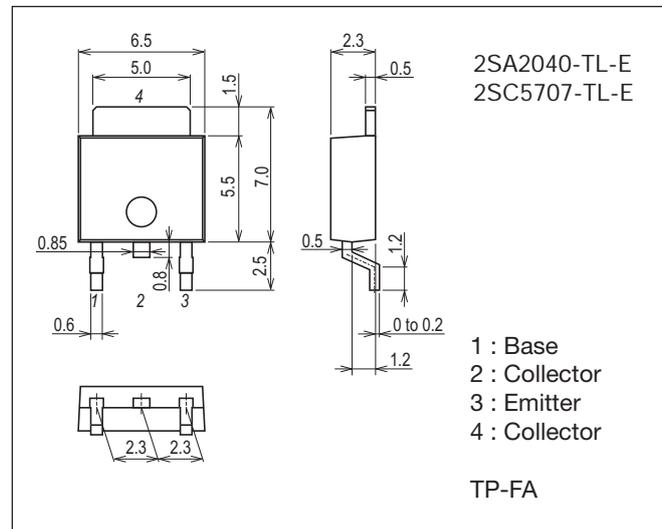
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		(-50)100	V
Collector-to-Emitter Voltage	V <sub>CES</sub>		(-50)100	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(-50)	V
Emitter-to-Base Voltage	V <sub>EB0</sub>		(-6)	V
Collector Current	I <sub>C</sub>		(-8)	A
Collector Current (Pulse)	I <sub>CP</sub>		(-11)	A

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#### Package Dimensions unit : mm (typ) 7518-003



#### Package Dimensions unit : mm (typ) 7003-003

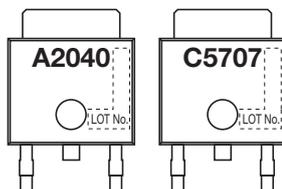


### Product & Package Information

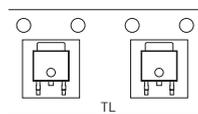
- Package : TP
- JEITA, JEDEC : SC-64, TO-251
- Minimum Packing Quantity : 500 pcs./bag

- Package : TP-FA
- JEITA, JEDEC : SC-63, TO-252
- Minimum Packing Quantity : 700 pcs./reel

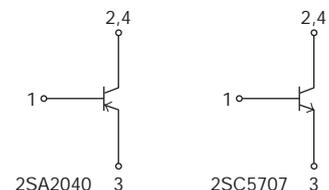
### Marking (TP, TP-FA)



### Packing Type (TP-FA) : TL



### Electrical Connection



## 2SA2040 / 2SC5707

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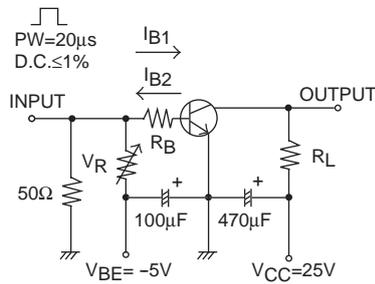
Parameter	Symbol	Conditions	Ratings	Unit
Base Current	$I_B$		(-)2	A
Collector Dissipation	$P_C$		1.0	W
		$T_C=25^\circ\text{C}$	15	W
Junction Temperature	$T_j$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-)40\text{V}, I_E=0\text{A}$			(-)0.1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-)4\text{V}, I_C=0\text{A}$			(-)0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=(-)2\text{V}, I_C=(-)500\text{mA}$	200		560	
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-)10\text{V}, I_C=(-)500\text{mA}$		(290)330		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(50)28		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=(-)3.5\text{A}, I_B=(-)175\text{mA}$		(-230)160	(-390)240	mV
	$V_{CE(sat)2}$	$I_C=(-)2\text{A}, I_B=(-)40\text{mA}$		(-240)110	(-400)170	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)2\text{A}, I_B=(-)40\text{mA}$		(-)0.83	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0\text{A}$	(-50)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=(-)100\mu\text{A}, R_{BE}=0\Omega$	(-50)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0\text{A}$	(-)6			V
Turn-On Time	$t_{on}$			(40)30		ns
Storage Time	$t_{stg}$	See specified Test Circuit.		(225)420		ns
Fall Time	$t_f$			25		ns

### Switching Time Test Circuit



$$20I_{B1} = -20I_{B2} = I_C = 2.5\text{A}$$

For PNP, the polarity is reversed.

### Ordering Information

Device	Package	Shipping	memo
2SA2040-E	TP	500pcs./bag	Pb Free
2SC5707-E	TP	500pcs./bag	
2SA2040-TL-E	TP-FA	700pcs./reel	
2SC5707-TL-E	TP-FA	700pcs./reel	